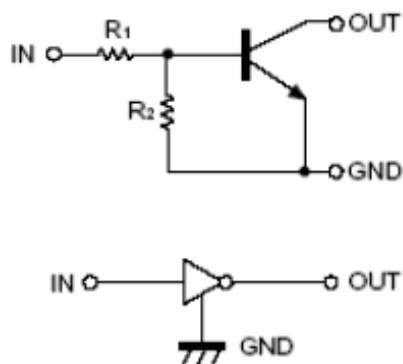


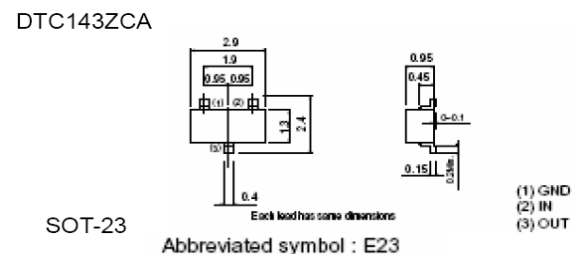
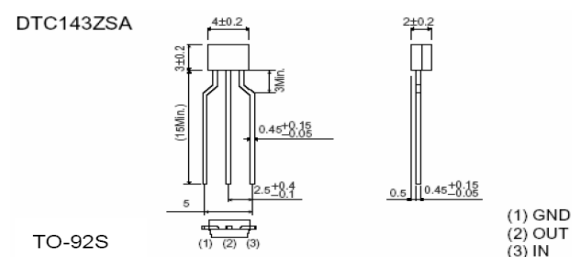
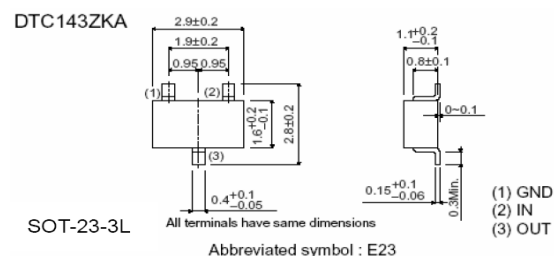
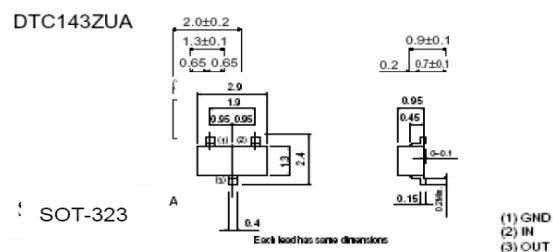
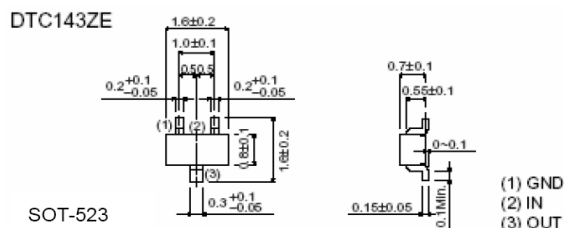
DIGITAL TRANSISTOR (NPN)

FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.



Digital Transistor (built-in resistor)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbols	Limits (DTC143Z□)					UNITS
		E	UA	CA	KA	SA	
Collector-Base Voltage	$V_{(BR)CBO}$			50			V
Collector-Emitter Voltage	$V_{(BR)CEO}$			50			V
Emitter-Base Voltage	$V_{(BR)EBO}$			5			V
Collector Current	I_C			100			mA
Collector Power Dissipation	P_C	150		200		300	mW
Junction Temperature	T_j			150			°C
Storage Temperature	T_{stg}			-55~150			°C

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Input Voltage	$V_{I(off)}$ $V_{I(on)}$	$V_{CC}=5V, I_O=100\mu A$ $V_O=0.3V, I_O=5mA$	0.5		1.3	V
Output Voltage	$V_{O(on)}$	$I_O/I_I=5mA/0.25mA$		0.1	0.3	V
Input Current	I_I	$V_I=5V$			1.8	mA
Output Current	$I_{O(off)}$	$V_{CC}=50V, V_I=0$			0.5	μA
DC Current Gain	G_I	$V_O=5V, I_O=10mA$	80			
Input Resistance	R_1		3.29	4.7	6.11	K Ω
Resistance Ratio	R_2/R_1		8	10	12	
Transition Frequency	f_T	$V_{CE}=10V, I_E=-5mA,$ $f=100MHz$		250		MHz